

**2SA984,  
984K**



2003A

PNP/NPN Epitaxial Planar  
Silicon Transistors

**2SC2274,  
2274K**

**Low Frequency Power Amp  
Applications**

©465F

**Features**

- . High breakdown voltage ( $V_{CE0} \geq 50/80V$ ).
- . High current ( $I_C = 500mA$ ).
- . Low saturation voltage.

( ): 2SA984,984K

Absolute Maximum Ratings at Ta=25°C		A984,C2274	A984K,C2274K	unit
Collector to Base Voltage	$V_{CBO}$	(-) 60	(-) 100	V
Collector to Emitter Voltage	$V_{CEO}$	(-) 50	(-) 80	V
Emitter to Base Voltage	$V_{EBO}$		(-) 5	V
Collector Current	$I_C$		(-) 500	mA
	$i_{cp}$		(-) 800	mA
Collector Dissipation	$P_C$		600	mW
Junction Temperature	$T_j$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

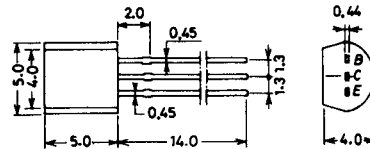
**Electrical characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-) 40V, I_E = 0$			(-) 1.0	uA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-) 4V, I_C = 0$			(-) 1.0	uA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-) 5V, I_C = (-) 50mA$		60*	320*	
	$h_{FE(2)}$	$V_{CE} = (-) 5V, I_C = (-) 400mA$ (pulse)		35		
G-B Product	$f_T$	$V_{CE} = (-) 10V, I_C = (-) 10mA$		120		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = (-) 10V, f = 1MHz$		(9)		pF
				5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-) 400mA, I_B = (-) 40mA$			(-0.25) (-0.6)	V
B-E Saturation Voltage	$V_{BE(sat)}$	" "			0.2 0.6	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10uA, I_E = 0$			(-) 0.9 (-) 1.2	V
		A984, C2274			(-) 60	V
		A984K, C2274K			(-) 100	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-) 1mA, R_{BE} = open$			(-) 50	V
		A984K, C2274K			(-) 80	V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-) 10uA, I_C = 0$			(-) 5	V

\* The 2SA984,K, 2SC2274,K are classified by 50mA  $h_{FE}$  as follows.

60	D	120	100	E	200	160	F	320
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**Case Outline 2003A  
(unit:mm)**



JEDEC: TO-92      B: Base  
EIAJ: SC-43      C: Collector  
SANYO: NP      E: Emitter

For details, refer to the description of the 2SC2274, 2274K.

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